Atty. Docket No. Q77826

AMENDMENT UNDER 37 C.F.R. § 1.111

U.S. Appln. No.: 10/676,032

**AMENDMENTS TO THE CLAIMS** 

This listing of claims will replace all prior versions and listings of claims in the

application:

**LISTING OF CLAIMS:** 

Claims 1-6 (canceled).

7. (currently amended): A coating apparatus for removing edge pool formed on a wafer

side surface of a coating film deposited on a wafer by edge rinse treatment using a rinse solution,

comprising:

a mechanism in which the edge rinse treatment is performed using any one selected from

solvents having different dissolving rates for dissolving the coating film, the any one selected

from solvents being used as the rinse solution,

wherein the mechanism comprises a plurality of rinse nozzles for supplying the solvents

having different dissolving rates for dissolving the coating film.

8. (original): The coating apparatus according to Claim 7,

wherein the dissolving rates vary in accordance with types of coating film, and the any

one selected from the solvents minimizes an edge hump of the coating film.

9. (canceled).

2

Atty. Docket No. Q77826

AMENDMENT UNDER 37 C.F.R. § 1.111

U.S. Appln. No.: 10/676,032

10. (original): The coating apparatus according to Claim 7, wherein the coating film is an organic antireflection film or a photoresist film.

11. (original): The coating apparatus according to Claim 10, wherein the solvents comprise isopropyl alcohol and polyethylene glycol monomethyl ether acetate.

12. (withdrawn): A coating method for forming a coating film on a wafer and for removing for removing edge pool formed on a wafer side surface by edge rinse treatment using a rinse solution, the method comprising:

a mixing step of mixing solvents having different dissolving rates for dissolving the coating film, the solvents being used as the rinse solution.

13. (withdrawn): The coating method according to Claim 12,

wherein the dissolving rates vary in accordance with types of coating film, and the mixing step is performed so that the rinse solution minimizes an edge hump of the coating film.

- 14. (withdrawn): The coating method according to Claim 12, wherein the coating film is an organic antireflection film or a photoresist film.
- 15. (withdrawn): The coating apparatus according to Claim 14,

wherein the solvents comprise isopropyl alcohol and polyethylene glycol monomethyl ether acetate.

16. (withdrawn): A coating method for forming a coating film on a wafer and for removing for removing edge pool formed on a wafer side surface by edge rinse treatment using a rinse solution, the method comprising:

a selecting step of selecting any one of solvents having different dissolving rates for dissolving the coating film, the any one of solvents being used as the rinse solution.

17. (withdrawn): The coating method according to Claim 16,

wherein the dissolving rates vary in accordance with types of coating film, and the selecting step is performed so that the rinse solution minimizes an edge hump of the coating film.

- 18. (withdrawn): The coating method according to Claim 16, wherein the coating film is an organic antireflection film or a photoresist film.
- 19. (withdrawn): The coating method according to Claim 18,

wherein the solvents comprise isopropyl alcohol and polyethylene glycol monomethyl ether acetate.